

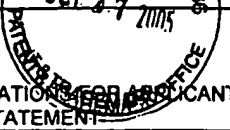


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APPLICANT:
Abraham et al.

FILING DATE:
June 11, 2004

GROUP:
2818

[illegible]

FORM PTO-1449 (Modified)				ATTY. DOCKET NO. FIS920040017US1		SERIAL NO. 10/709,999	
LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT				APPLICANT: Abraham et al.			
(Use several sheets if necessary)				FILING DATE: June 11, 2004		GROUP: 2818	
FOREIGN PATENT DOCUMENTS							
		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION
							YES NO
OTHER ART (Including Author, Title, Date, Pertinent Pages, etc.)							
	CA	Abraham et al., "A 0.18um Logic-Based MRAM Technology for High Performance Nonvolatile Memory Applications," VLSI Conference, IEEE Journal of Solid State Circuits Society, 2003.					
	CB	Chen et al. "Magnetic Tunnel Junction Pattern Technique", Journal of Applied Physics, Vol. 93, no. 10, 2003					
	CC	DeBrosse et al. "A High-Speed 128Kbit MRAM Core For Future Universal Memory Applications," VLSI Conference, IEEE Journal of Solid State Circuits Society, 2003.					
EXAMINER 				DATE CONSIDERED 4/2006			
EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							